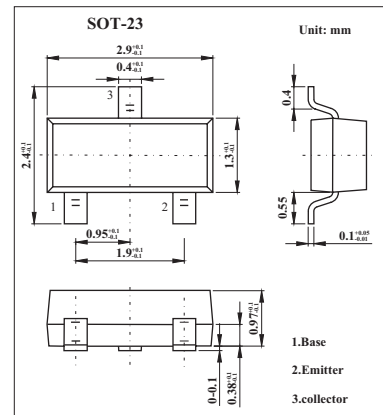


2SA1365

■ Features

- Low collector to emitter saturation voltage.
- Excellent linearity of DC forward current gain.
- Super mini package for easy mounting.
- High collector current.
- High gain band width product.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	-25	V
Collector-emitter voltage	V _{CEO}	-20	V
Emitter-base voltage	V _{EBO}	-4	V
Peak collector current	I _{CM}	-1	A
Collector current	I _C	-700	mA
Collector dissipation (Ta=25°C)	P _C	150	mW
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-55 to +125	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V (BR) CBO	I _C = -10 μA, I _E = 0	-25			V
Collector-emitter breakdown voltage	V (BR) CEO	I _C = -100 μA, R _{BE} = ∞	-20			V
Emitter-base breakdown voltage	V (BR) EBO	I _E = -10 μA, I _C = 0	-4			V
Collector cut-off current	I _{CBO}	V _{CB} = -25 V, I _E = 0			-1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -2 V, I _C = 0			-1	μA
DC current gain (*)	h _{FE}	V _{CE} = -4 V, I _C = -100 mA	150		800	
Collector-emitter saturation voltage	V _{CE}	I _C = -500 mA, I _B = -25 mA		-0.2	-0.5	V
Gain band width product	f _T	V _{CE} = -6 V, I _E = 10 mA		180		MHz

* It shows h_{FE} classification in right table.

■ h_{FE} Classification

Marking	AE	AF	AG
h _{FE}	150~300	250~500	400~800